TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT8G134

## Strobe Flash Applications

- Compact and Thin (TSSOP-8) package
- Enhancement-mode
- Peak collector current:  $I_C = 150 \text{ A (max)}$

(@VGE=2.5V(min))/

## Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage	V <sub>CES</sub>	400	V		
Gate-emitter voltage	DC	V <sub>GES</sub>	± 4	V	
	Pulse	$V_{GES}$	± 5		
Collector current	Pulse (Note 1)	I <sub>CP</sub>	150	А	
Collector power dissipation (t=10 s)	(Note 2a)	P <sub>C</sub> (1)	1.1	W	
	(Note 2b)	P <sub>C</sub> (2)	0.6	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

lead (Pb)-free package or lead (Pb)-free finish.

Characteristics	Symbol	Rating	Unit	
Thermal resistance , junction to ambient (t = 10 s) (Note2a)	R <sub>th (j-a)</sub> (1)	114	°C/W	
Thermal resistance , junction to ambient (t = 10 s) (Note2b)	R <sub>th (j-a)</sub> (2)	208	°C/W	

#### Marking (Note 3)

Note: For (Note 1), (Note 2a), (Note 2b) and (Note 3), Please refer to the next page.

Part No. (or abbreviation code)

8G134

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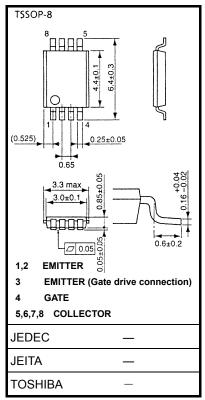
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But 1

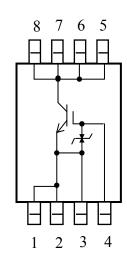
Lot No. A line indicates

Unit: mm



Weight: 0.035 g (typ.)

# **Circuit Configuration**



## **Electrical Characteristics (Ta = 25°C)**

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 4 \text{ V}, V_{CE} = 0$	_	_	± 10	μА
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 400 V, V <sub>GE</sub> = 0		_	10	μΑ
Gate-emitter cut-off voltage		V <sub>GE</sub> (OFF)	I <sub>C</sub> = 1 mA, V <sub>CE</sub> = 5 V	0.65	1.0	1.35	٧
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 150 A, V <sub>GE</sub> = 2.5 V		3.4		>
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz		4560		pF
Switching time	Rise time	t <sub>r</sub>	$\begin{array}{c} 3 \ \text{V} \\ 0 \\ \end{array}$ $\begin{array}{c} 62 \ \Omega \\ \text{O-W} \\ \end{array}$ $\begin{array}{c} 62 \ \Omega \\ \text{V}_{\text{IN}} \text{: } t_r \leq 100 \text{ ns} \\ \text{t}_f \leq 100 \text{ ns} \\ \text{Duty cycle} \leq 1\% \\ \end{array}$	_	0.6	_	- μs
	Turn-on time	t <sub>on</sub>			0.8		
	Fall time	t <sub>f</sub>			1.2		
	Turn-off time	t <sub>off</sub>			1.8		

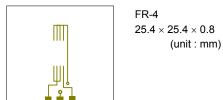
#### Note

Note 1: Please use devices on condition that the junction temperature is below 150°C. Repetitive rating: pulse width limited by maximum junction temperature.

Note 2a : Device mounted on a glass-epoxy board (a)

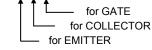
FR-4 25.4 × 25.4 × 0.8 (unit : mm)

25.4 × 0.8 (unit : mm)



Note 2b: Device mounted on

a glass-epoxy board (b)



Note 3: O on lower right of the marking indicates Pin 1.

Weekly code: (Three digits)

Week of manufacture
(01 for first week of year, continues up to 52 or 53)

Year of manufacture
(One low-order digits of calendar year)

Pb-Free Finish (Only a coating lead terminal):

It is marking about an underline to a week of manufacture mark.



### **Caution on handling**

This device is MOS gate type. Therefore, please care of a protection from ESD in your handling.

# Caution in design

You should be design dV/dt value under lcp=150A is below 400 V/ $\mu$ s when IGBT turn off under Ta=70°C . You should be design to don't flow collector current through terminal number 3 .

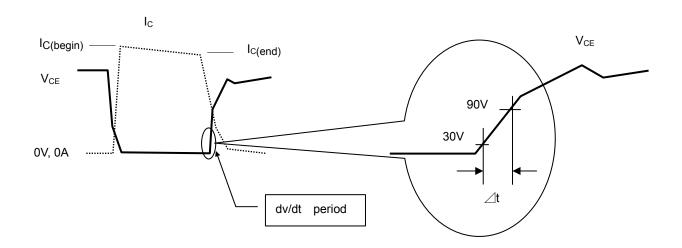
#### definition of dv/dt

The slope of V<sub>CE</sub> from 30v to 90v (attached figure.1)

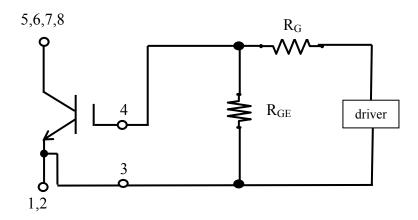
$$dv/dt = (90V-30V) / (\triangle t)$$
$$= 60V / \triangle t$$

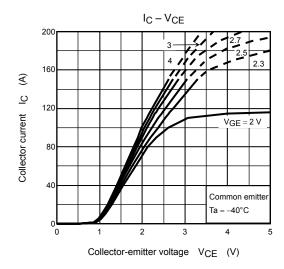
waveform

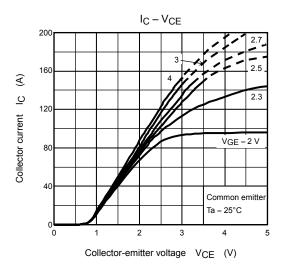
•waveform (expansion)

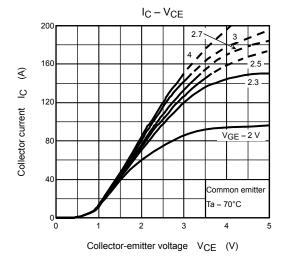


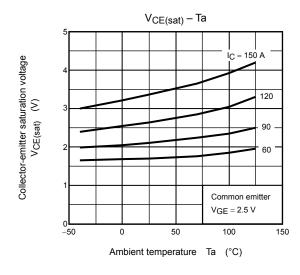
Gate drive connection

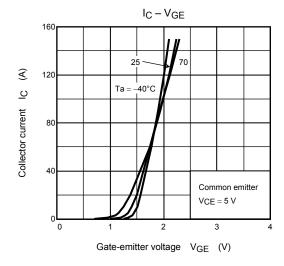


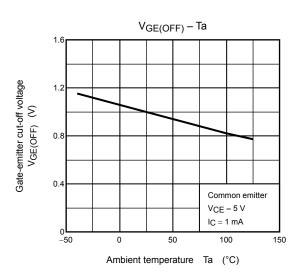


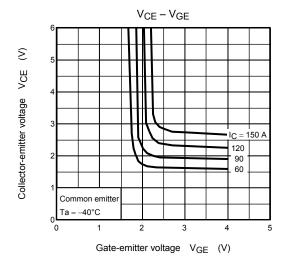


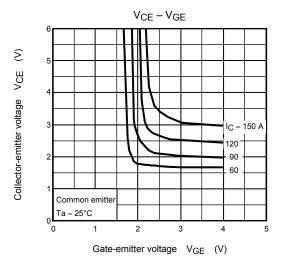


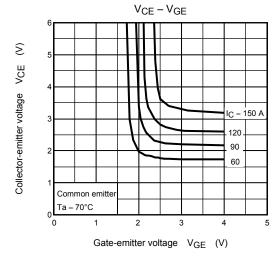


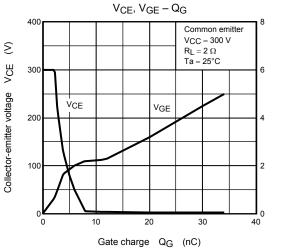




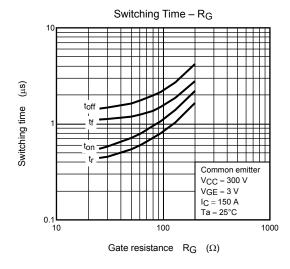


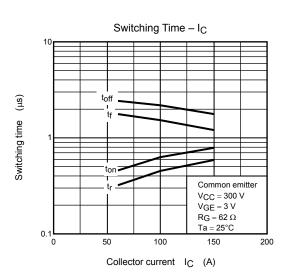


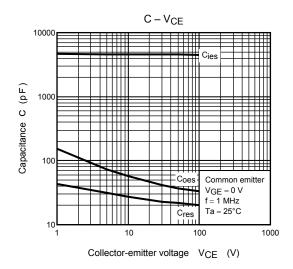


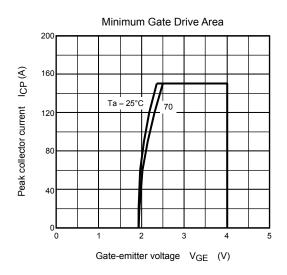


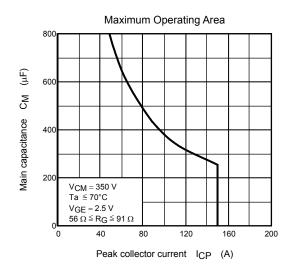












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